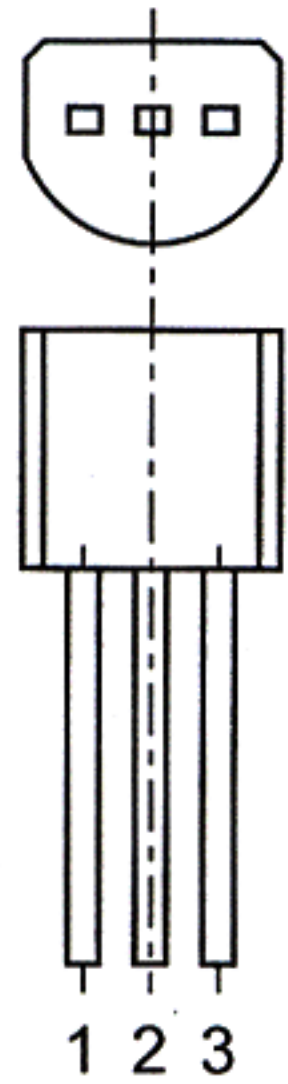


TO-92 Plastic-Encapsulate Transistors

KTC3192 TRANSISTOR(NPN)



TO-92

1.EMITTER

2.COLLECTOR

3.BASE

FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

T_J : $150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	4		V
Collector cut-off current	I_{CBO}	$V_{CB} = 35 V, I_E = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$		1.0	μA
DC current gain	h_{FE}	$V_{CE} = 12 V, I_C = 2 mA$	40	240	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 10 mA, I_B = 1 mA$		0.4	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 10 mA, I_B = 1 mA$		1.0	V
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 1 mA$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240